

# **Excellent Integrated System Limited**

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Vishay/Siliconix SQJ463EP-T1-GE3

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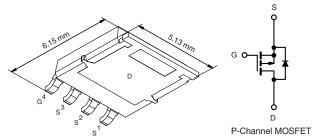
## SQJ463EP

Vishay Siliconix

## Automotive P-Channel 40 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY                            |        |
|--|--------|
| V <sub>DS</sub> (V)                        | - 40   |
| $R_{DS(on)} (\Omega)$ at $V_{GS}$ = - 10 V | 0.010  |
| $R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$ | 0.015  |
| I <sub>D</sub> (A)                         | - 30   |
| Configuration                              | Single |

#### PowerPAK<sup>®</sup> SO-8L Single



### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- AEC-Q101 Qualified<sup>d</sup>
- 100 % R<sub>g</sub> and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



COMPLIANT HALOGEN

| ORDERING INFORMATION            |                 |
|---------------------------------|-----------------|
| Package                         | PowerPAK SO-8L  |
| Lead (Pb)-free and Halogen-free | SQJ463EP-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS                                  | (T <sub>C</sub> = 25 °C, unless | otherwise noted                   | )             |      |  |
|---|---------------------------------|-----------------------------------|---------------|------|--|
| PARAMETER   |                                 | SYMBOL                            | LIMIT         | UNIT |  |
| Drain-Source Voltage                                      |                                 | V <sub>DS</sub>                   | - 40          | М    |  |
| Gate-Source Voltage                                       |                                 | V <sub>GS</sub>                   | ± 20          | V    |  |
| Continuous Drain Current <sup>a</sup>                     | T <sub>C</sub> = 25 °C          |                                   | - 30          |      |  |
| Continuous Drain Currenta                                 | T <sub>C</sub> = 125 °C         | I <sub>D</sub>                    | - 30          |      |  |
| Continuous Source Current (Diode Conduction) <sup>a</sup> |                                 | I <sub>S</sub>                    | - 30          | А    |  |
| Pulsed Drain Current <sup>b</sup>                         |                                 | I <sub>DM</sub>                   | - 120         |      |  |
| Single Pulse Avalanche Current                            |                                 | I <sub>AS</sub>                   | - 44          |      |  |
| L = 0.1 mH  |                                 | E <sub>AS</sub>                   | 97            | mJ   |  |
| Mariana Davies Diasia stiant                              | T <sub>C</sub> = 25 °C          | P                                 | 83            | 14/  |  |
| Maximum Power Dissipation <sup>b</sup>                    | T <sub>C</sub> = 125 °C         | P <sub>D</sub>                    | 28            | W    |  |
| Operating Junction and Storage Temperature Range          |                                 | T <sub>J</sub> , T <sub>stg</sub> | - 55 to + 175 | *0   |  |
| Soldering Recommendations (Peak Temperat                  | ure) <sup>e, f</sup>            |                                   | 260           | °C   |  |

| THERMAL RESISTANCE RATINGS |                        |                   |       |      |
|----------------------------|------------------------|-------------------|-------|------|
| PARAMETER                  |                        | SYMBOL            | LIMIT | UNIT |
| Junction-to-Ambient        | PCB Mount <sup>c</sup> | R <sub>thJA</sub> | 65    | °C/W |
| Junction-to-Case (Drain)   |                        | R <sub>thJC</sub> | 1.8   | 0/10 |

#### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

- e. See Solder Profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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## SQJ463EP

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| <b>SPECIFICATIONS</b> ( $T_C = 25 \ ^{\circ}C$ , | unless other             | wise noted)   |  |       |       |       |      |
|--|--------------------------|---|--|-------|-------|-------|------|
| PARAMETER  | SYMBOL                   | TES   | T CONDITIONS   | MIN.  | TYP.  | MAX.  | UNIT |
| Static   | •                        |   |  |       |       | •     |      |
| Drain-Source Breakdown Voltage                   | V <sub>DS</sub>          | V <sub>GS</sub>   | = 0, I <sub>D</sub> = - 250 μA                             | - 40  | -     | -     | v    |
| Gate-Source Threshold Voltage                    | V <sub>GS(th)</sub>      | V <sub>DS</sub> =   | V <sub>GS</sub> , I <sub>D</sub> = - 250 μA                | - 1.5 | - 2.0 | - 2.5 | v    |
| Gate-Source Leakage                              | I <sub>GSS</sub>         | V <sub>DS</sub> =   | = 0 V, V <sub>GS</sub> = ± 20 V                            | -     | -     | ± 100 | nA   |
|  |                          | $V_{GS} = 0 V$  | V <sub>DS</sub> = - 40 V                                   | -     | -     | - 1   |      |
| Zero Gate Voltage Drain Current                  | I <sub>DSS</sub>         | $V_{GS} = 0 V$  | $V_{DS}$ = - 40 V, $T_{J}$ = 125 °C                        | -     | -     | - 50  | μA   |
|  |                          | $V_{GS} = 0 V$  | V <sub>DS</sub> = - 40 V, T <sub>J</sub> = 175 °C          | -     | -     | - 150 |      |
| On-State Drain Current <sup>a</sup>              | I <sub>D(on)</sub>       | V <sub>GS</sub> = - 10 V                                  | $V_{DS} \le -5 V$  | - 30  | -     | -     | Α    |
|  |                          | $V_{GS} = -10 V$  | I <sub>D</sub> = - 18 A                                    | -     | 0.008 | 0.010 |      |
|  |                          | $V_{GS} = -4.5 V$   | I <sub>D</sub> = - 15 A                                    | -     | 0.012 | 0.015 | Ω    |
| Drain-Source On-State Resistance <sup>a</sup>    | R <sub>DS(on)</sub>      | V <sub>GS</sub> = - 10 V                                  | I <sub>D</sub> = - 18 A; T <sub>J</sub> = 125 °C           | -     | 0.013 | 0.015 |      |
|  |                          | V <sub>GS</sub> = - 10 V                                  | I <sub>D</sub> = - 18 A; T <sub>J</sub> = 175 °C           | -     | 0.015 | 0.018 |      |
| Forward Transconductanceb                        | g <sub>fs</sub>          | V <sub>DS</sub> =   | V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 18 A          |       | 45    | -     | S    |
| Dynamic <sup>b</sup>                             |                          |   |  |       | •     | •     | •    |
| Input Capacitance                                | C <sub>iss</sub>         |   |  | -     | 4700  | 5875  |      |
| Output Capacitance                               | C <sub>oss</sub>         | $V_{GS} = 0 V$  | V <sub>DS</sub> = - 20 V, f = 1 MHz                        | -     | 630   | 790   | pF   |
| Reverse Transfer Capacitance                     | C <sub>rss</sub>         |   |  | -     | 460   | 575   |      |
| Total Gate Charge <sup>c</sup>                   | Qg                       |   |  | -     | 98    | 150   |      |
| Gate-Source Charge <sup>c</sup>                  | Q <sub>gs</sub>          | V <sub>GS</sub> = - 10 V                                  | V <sub>DS</sub> = - 20 V, I <sub>D</sub> = - 18.6 A        | -     | 14    | -     | nC   |
| Gate-Drain Charge <sup>c</sup>                   | Q <sub>gd</sub>          |   |  | -     | 23    | -     |      |
| Gate Resistance                                  | Rg                       |   | f = 1 MHz  |       | 2.3   | 3.2   | Ω    |
| Turn-On Delay Time <sup>c</sup>                  | t <sub>d(on)</sub>       |   |  | -     | 21    | 32    |      |
| Rise Time <sup>c</sup>                           | t <sub>r</sub>           |   | $V_{DD} = -20 \text{ V}, \text{ R}_{\text{I}} = 20 \Omega$ |       | 17    | 26    | - ns |
| Turn-Off Delay Time <sup>c</sup>                 | t <sub>d(off)</sub>      | $I_D \cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 $\Omega$ |  | -     | 121   | 182   |      |
| Fall Time <sup>c</sup>                           | t <sub>f</sub>           |   |  | -     | 51    | 77    |      |
| Source-Drain Diode Ratings and Char              | acteristics <sup>b</sup> | ·   |  |       |       |       |      |
| Pulsed Current <sup>a</sup>                      | I <sub>SM</sub>          |   |  | -     | -     | - 120 | Α    |
| Forward Voltage                                  | V <sub>SD</sub>          | I <sub>F</sub> =  | - 4.5 A, V <sub>GS</sub> = 0                               | -     | - 0.8 | - 1.2 | V    |
|  |                          |   |  |       |       |       |      |

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



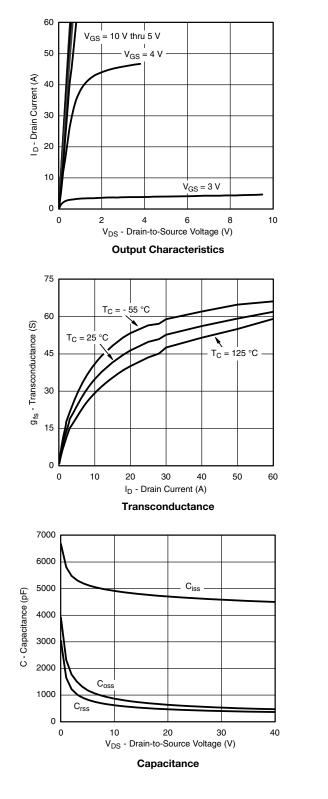


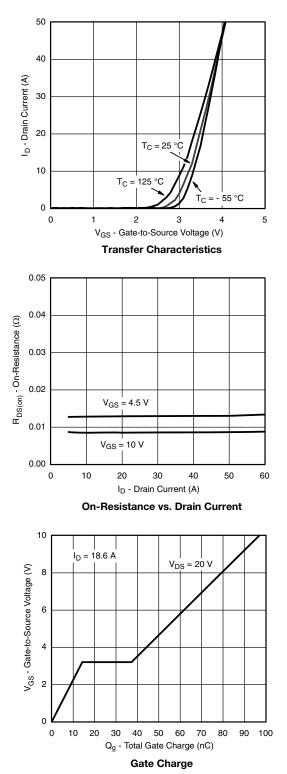
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### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)





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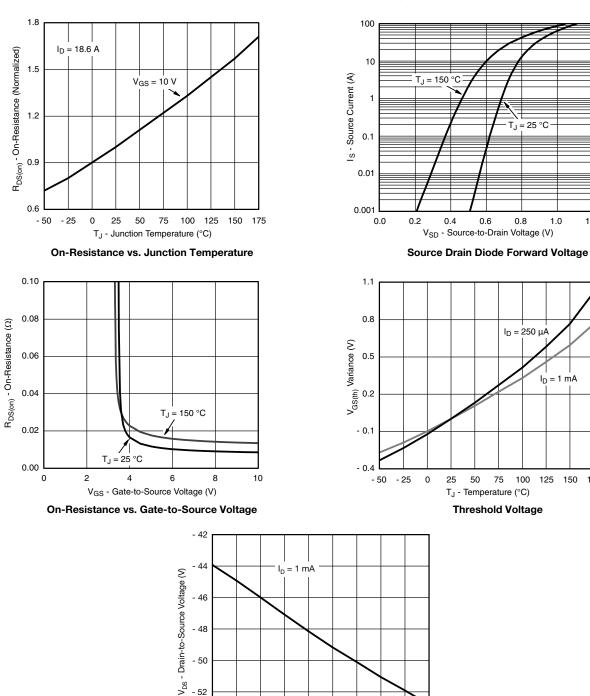
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1.0

1.2

150 175



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**Drain Source Breakdown vs. Junction Temperature** 

T<sub>,I</sub> - Junction Temperature (°C)

- 54 🖵 - 50

- 25 0 25 50 75 100 125 150 175

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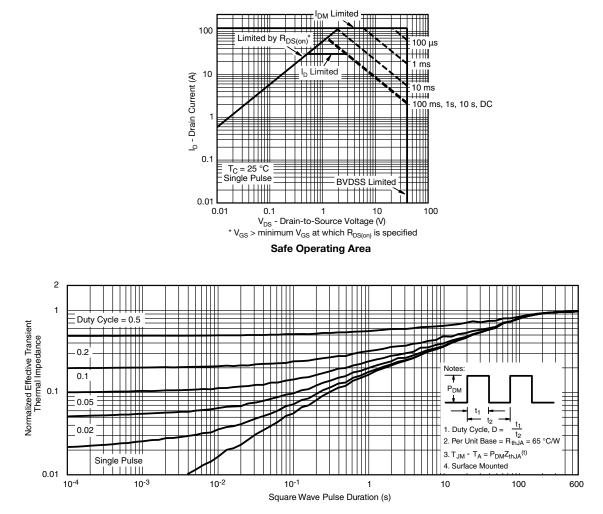


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**THERMAL RATINGS** ( $T_C = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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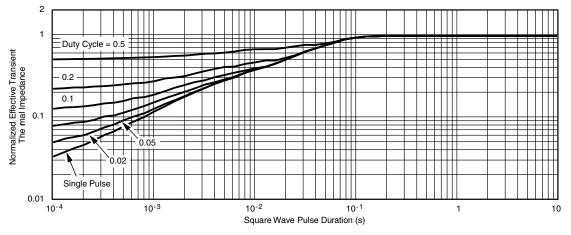


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### **THERMAL RATINGS** ( $T_C = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?65540">www.vishay.com/ppg?65540</a>.

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### **Ordering Information**

**Vishay Siliconix** 

## PowerPAK<sup>®</sup> SO-8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

| ATASHEET PART NUMBER | OLD ORDERING CODE <sup>a</sup> | NEW ORDERING CODE |  |
|----------------------|--------------------------------|-------------------|--|
| SQJ200EP             | -                              | SQJ200EP-T1_GE3   |  |
| SQJ202EP             | -                              | SQJ202EP-T1_GE3   |  |
| SQJ401EP             | SQJ401EP-T1-GE3                | SQJ401EP-T1_GE3   |  |
| SQJ402EP             | SQJ402EP-T1-GE3                | SQJ402EP-T1_GE3   |  |
| SQJ403EEP            | SQJ403EEP-T1-GE3               | SQJ403EEP-T1_GE3  |  |
| SQJ403EP             | -                              | SQJ403EP-T1_GE3   |  |
| SQJ410EP             | SQJ410EP-T1-GE3                | SQJ410EP-T1_GE3   |  |
| SQJ412EP             | SQJ412EP-T1-GE3                | SQJ412EP-T1_GE3   |  |
| SQJ416EP             | -                              | SQJ416EP-T1_GE3   |  |
| SQJ418EP             | -                              | SQJ418EP-T1_GE3   |  |
| SQJ422EP             | SQJ422EP-T1-GE3                | SQJ422EP-T1_GE3   |  |
| SQJ423EP             | -                              | SQJ423EP-T1_GE3   |  |
| SQJ431EP             | SQJ431EP-T1-GE3                | SQJ431EP-T1_GE3   |  |
| SQJ443EP             | SQJ443EP-T1-GE3                | SQJ443EP-T1_GE3   |  |
| SQJ444EP             | -                              | SQJ444EP-T1_GE3   |  |
| SQJ446EP             | -                              | SQJ446EP-T1_GE3   |  |
| SQJ456EP             | SQJ456EP-T1-GE3                | SQJ456EP-T1_GE3   |  |
| SQJ457EP             | -                              | SQJ457EP-T1 GE3   |  |
| SQJ459EP             | -                              | SQJ459EP-T1_GE3   |  |
| SQJ460AEP            | -                              | SQJ460AEP-T1_GE3  |  |
| SQJ461EP             | SQJ461EP-T1-GE3                | SQJ461EP-T1 GE3   |  |
| SQJ463EP             | SQJ463EP-T1-GE3                | SQJ463EP-T1_GE3   |  |
| SQJ465EP             | SQJ465EP-T1-GE3                | SQJ465EP-T1 GE3   |  |
| SQJ469EP             | SQJ469EP-T1-GE3                | SQJ469EP-T1_GE3   |  |
| SQJ474EP             | -                              | SQJ474EP-T1_GE3   |  |
| SQJ474EI<br>SQJ476EP | _                              | SQJ476EP-T1_GE3   |  |
| SQJ479EP             |                                | SQJ479EP-T1_GE3   |  |
| SQJ486EP             | -<br>SQJ486EP-T1-GE3           | SQJ486EP-T1_GE3   |  |
| SQJ488EP             | SQJ488EP-11-GE3                | SQJ488EP-T1_GE3   |  |
|                      |                                |                   |  |
| SQJ500AEP            | SQJ500AEP-T1-GE3               | SQJ500AEP-T1_GE3  |  |
| SQJ840EP             | SQJ840EP-T1-GE3                | SQJ840EP-T1_GE3   |  |
| SQJ844AEP            | SQJ844AEP-T1-GE3               | SQJ844AEP-T1_GE3  |  |
| SQJ850EP             | SQJ850EP-T1-GE3                | SQJ850EP-T1_GE3   |  |
| SQJ858AEP            | SQJ858AEP-T1-GE3               | SQJ858AEP-T1_GE3  |  |
| SQJ868EP             | -                              | SQJ868EP-T1_GE3   |  |
| SQJ886EP             | SQJ886EP-T1-GE3                | SQJ886EP-T1_GE3   |  |
| SQJ910AEP            | SQJ910AEP-T1-GE3               | SQJ910AEP-T1_GE3  |  |
| SQJ912AEP            | SQJ912AEP-T1-GE3               | SQJ912AEP-T1_GE3  |  |
| SQJ940EP             | SQJ940EP-T1-GE3                | SQJ940EP-T1_GE3   |  |
| SQJ942EP             | SQJ942EP-T1-GE3                | SQJ942EP-T1_GE3   |  |
| SQJ951EP             | SQJ951EP-T1-GE3                | SQJ951EP-T1_GE3   |  |
| SQJ952EP             | -                              | SQJ952EP-T1_GE3   |  |
| SQJ956EP             | SQJ956EP-T1-GE3                | SQJ956EP-T1_GE3   |  |
| SQJ960EP             | SQJ960EP-T1-GE3                | SQJ960EP-T1_GE3   |  |
| SQJ963EP             | SQJ963EP-T1-GE3                | SQJ963EP-T1_GE3   |  |
| SQJ968EP             | SQJ968EP-T1-GE3                | SQJ968EP-T1_GE3   |  |
| SQJ980AEP            | SQJ980AEP-T1-GE3               | SQJ980AEP-T1_GE3  |  |
| SQJ992EP             | SQJ992EP-T1-GE3                | SQJ992EP-T1_GE3   |  |

a. Old ordering code is obsolete and no longer valid for new orders

Revision: 01-Jul-16

Document Number: 65804

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### **Package Information**

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## PowerPAK<sup>®</sup> SO-8L Case Outline for Non-Al Parts

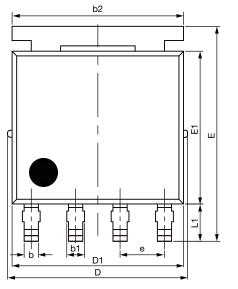
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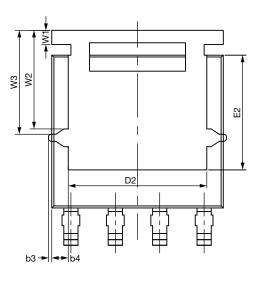
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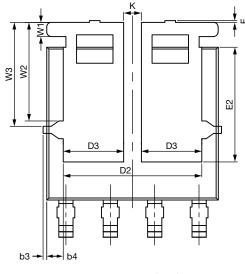
0.25 gauge line





Topside view

Backside view (single)



Backside view (dual)

Document Number: 69003

Revision: 16-May-16

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### **Package Information**

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| 5.14 | MILLIMETERS |          |       | INCHES    |       |       |  |
|------|-------------|----------|-------|-----------|-------|-------|--|
| DIM. | MIN.        | NOM.     | MAX.  | MIN.      | NOM.  | MAX.  |  |
| А    | 1.00        | 1.07     | 1.14  | 0.039     | 0.042 | 0.045 |  |
| A1   | 0.00        | -        | 0.127 | 0.00      | -     | 0.005 |  |
| b    | 0.33        | 0.41     | 0.48  | 0.013     | 0.016 | 0.019 |  |
| b1   | 0.44        | 0.51     | 0.58  | 0.017     | 0.020 | 0.023 |  |
| b2   | 4.80        | 4.90     | 5.00  | 0.189     | 0.193 | 0.197 |  |
| b3   |             | 0.094    |       |           | 0.004 |       |  |
| b4   |             | 0.47     |       |           | 0.019 |       |  |
| С    | 0.20        | 0.25     | 0.30  | 0.008     | 0.010 | 0.012 |  |
| D    | 5.00        | 5.13     | 5.25  | 0.197     | 0.202 | 0.207 |  |
| D1   | 4.80        | 4.90     | 5.00  | 0.189     | 0.193 | 0.197 |  |
| D2   | 3.86        | 3.96     | 4.06  | 0.152     | 0.156 | 0.160 |  |
| D3   | 1.63        | 1.73     | 1.83  | 0.064     | 0.068 | 0.072 |  |
| е    |             | 1.27 BSC | •     | 0.050 BSC |       |       |  |
| E    | 6.05        | 6.15     | 6.25  | 0.238     | 0.242 | 0.246 |  |
| E1   | 4.27        | 4.37     | 4.47  | 0.168     | 0.172 | 0.176 |  |
| E2   | 3.18        | 3.28     | 3.38  | 0.125     | 0.129 | 0.133 |  |
| F    | -           | -        | 0.15  | -         | -     | 0.006 |  |
| L    | 0.62        | 0.72     | 0.82  | 0.024     | 0.028 | 0.032 |  |
| L1   | 0.92        | 1.07     | 1.22  | 0.036     | 0.042 | 0.048 |  |
| К    |             | 0.51     | •     |           | 0.020 |       |  |
| W    |             | 0.23     |       | 0.009     |       |       |  |
| W1   | 0.41        |          |       | 0.016     |       |       |  |
| W2   | 2.82        |          |       | 0.111     |       |       |  |
| W3   | 2.96        |          |       | 0.117     |       |       |  |
| θ    | 0°          | -        | 10°   | 0°        | -     | 10°   |  |

#### Note

• Millimeters will gover

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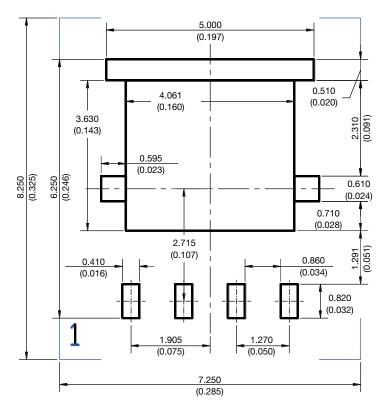


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### **PAD** Pattern

Vishay Siliconix

RECOMMENDED MINIMUM PAD FOR PowerPAK<sup>®</sup> SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12

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